

Fabrication of CMOS Integrated Circuits

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References

- John P. Uyemura, "Introduction to VLSI Circuits and Systems," 2002.
 - Chapter 4



Goal

Understand the fabrication (manufacturing) process for CMOS integrated circuits (ICs)



Silicon Wafer and Yield

Yield

$$- Y = \frac{N_G}{N_T} \times 100\%$$

- N_G : # good dies
- N_T : # total dies

$$- N_T = \pi \frac{(d-d_e)^2}{4A_{die}}$$

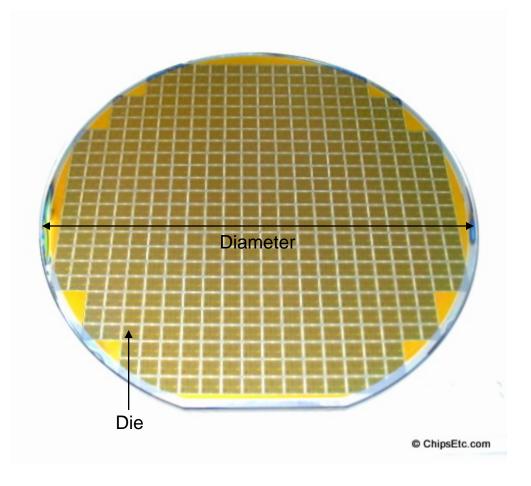
$$- Y = e^{-\sqrt{DA}}$$

- A: die area
- *D*: defect density

$$- Y = \left(1 - \frac{A_{die}D}{c}\right)^{c}$$

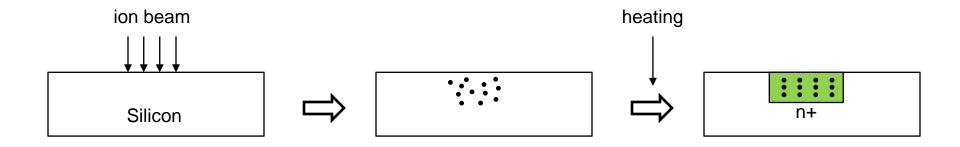
$$- Y = \frac{1}{\left(1 + \frac{A_{die}D}{c}\right)^2}$$

• c: a constant for clustered defects



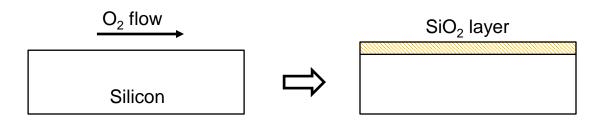


- Doped silicon layers
 - Ion implantation
 - Annealing

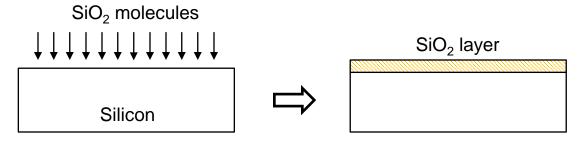




- Silicon Dioxide (insulator)
 - Thermal oxide

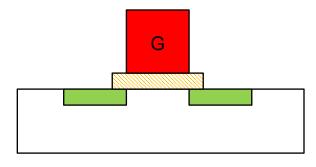


Chemical vapor deposition (CVD) oxide

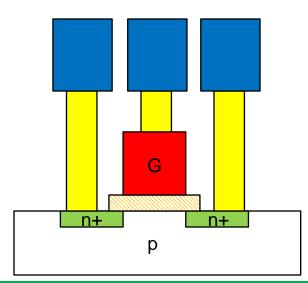




- Polycrystal Silicon
 - Used to fabricate Gate
 - Deposition

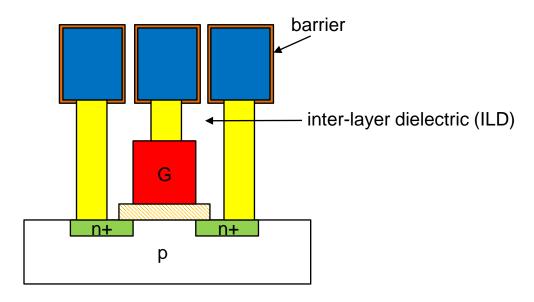


- Metal
 - Deposition



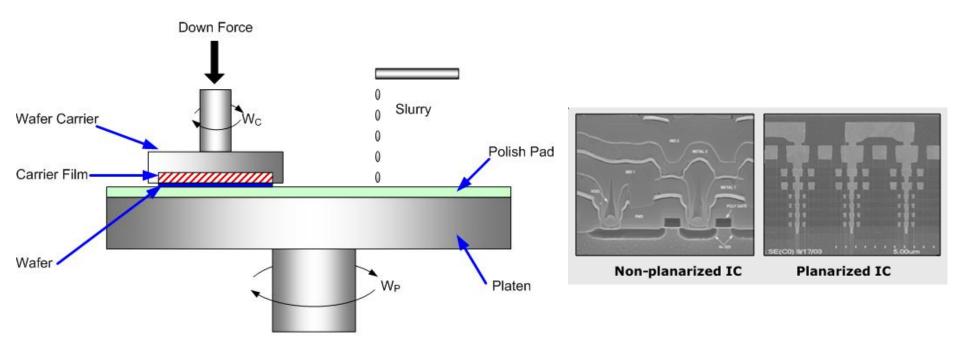


- Silicon Nitride
 - Barrier on the topmost layer
- Barrier is also used for preventing copper from diffusing into adjacent layers.





- Chemical-Mechanical Polishing (CMP)
 - also called Chemical-Mechanical Planarization
 - After depositing each layer, CMP is applied to planarize the surface.

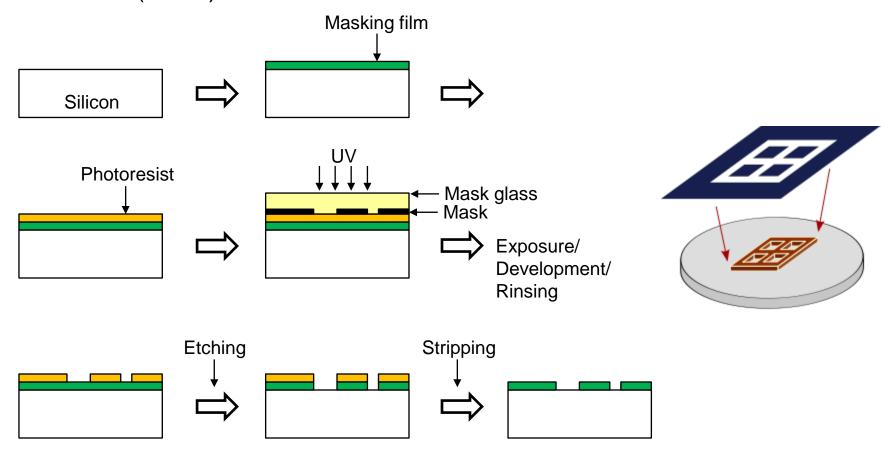




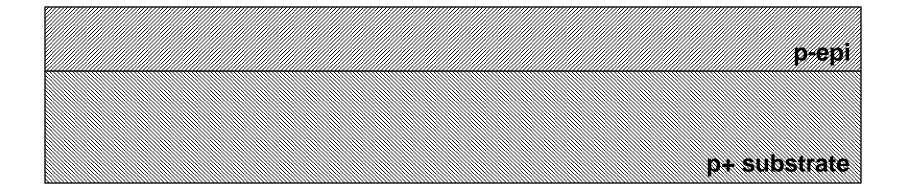
Source: http://www.ntu.edu.sg/home/mdlbutler/Research/cmp%20polisher.jpg Source: http://linx-consulting.com/images/planarized_IC.gif

Lithography (Photolithography)

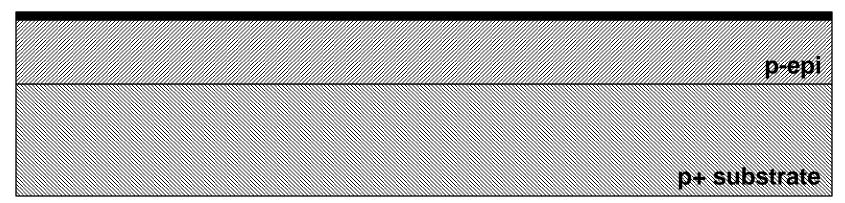
Reticle (mask)







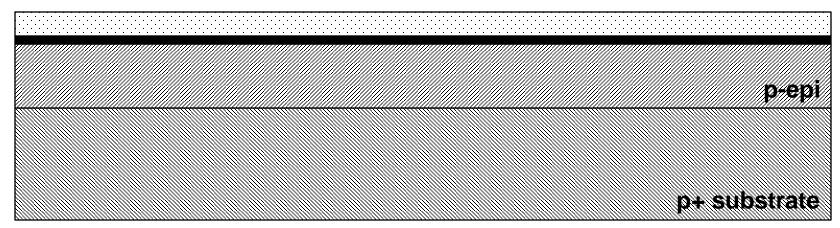




 SiO_2

Gate-oxide deposition

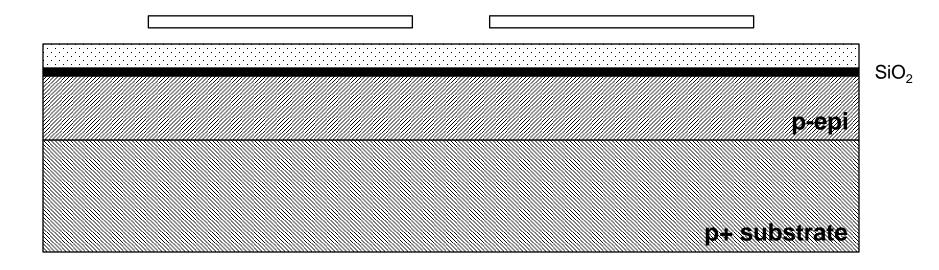




SiO₂

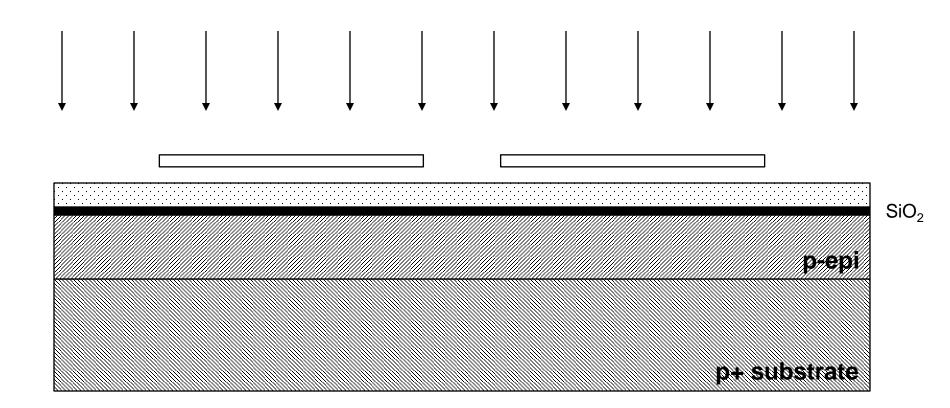
Photoresist





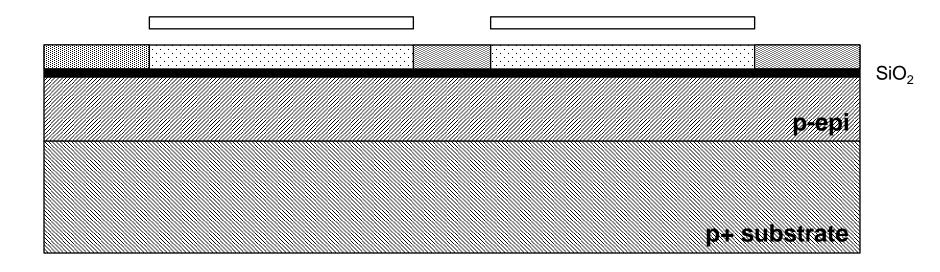
Mask





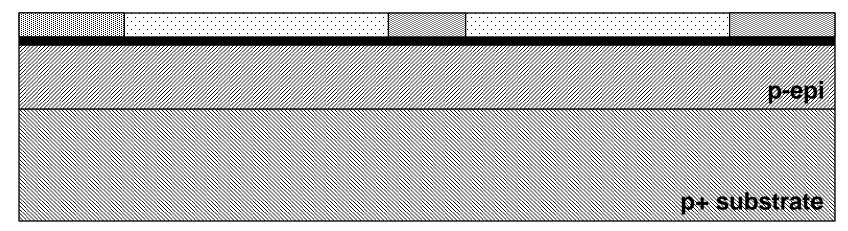
Expose (photolithography)





After photolithography

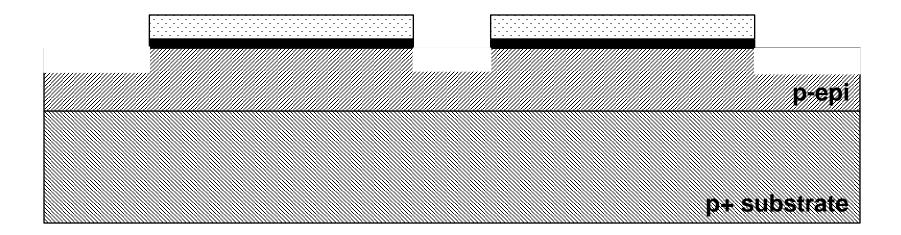




 SiO_2

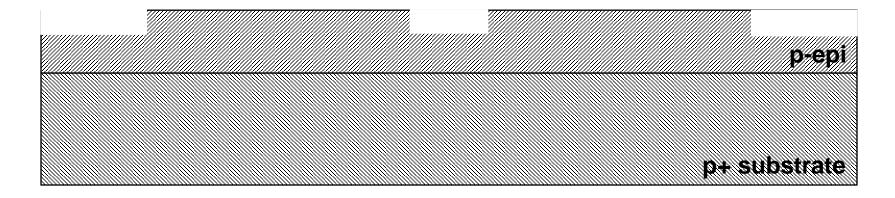
Remove mask





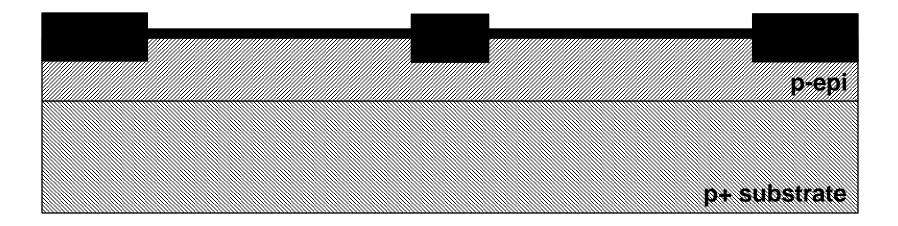
Etching





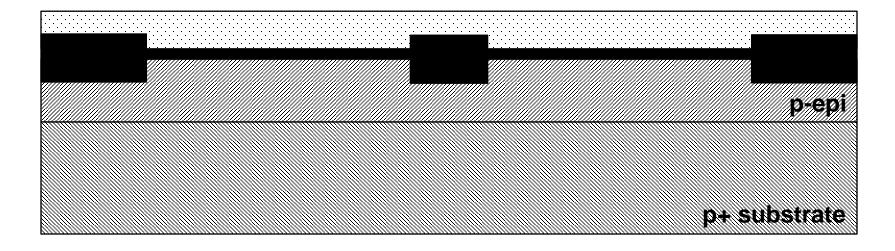
Etching





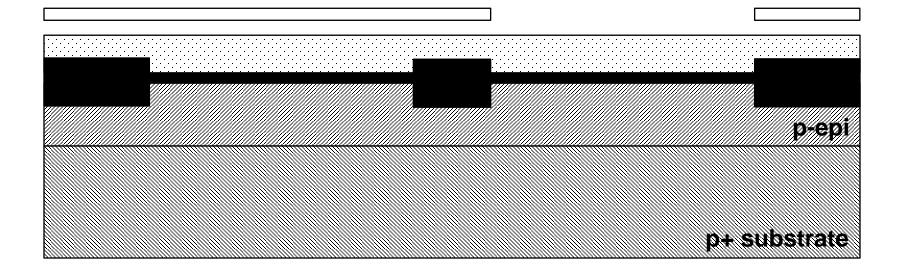
Oxide deposition





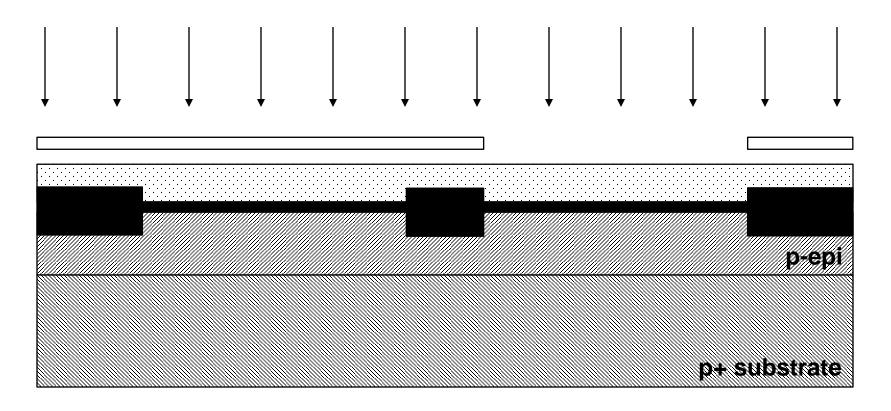
Photoresist





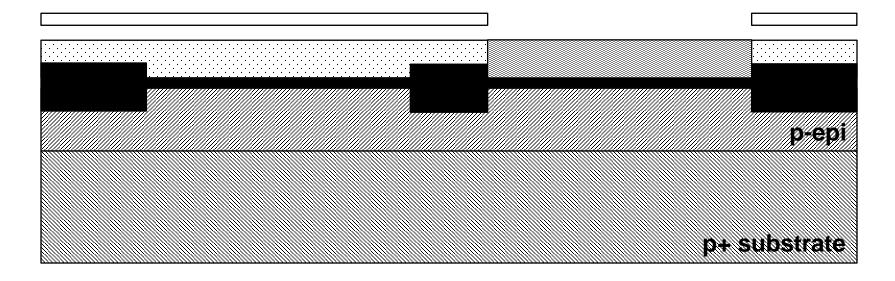
Mask





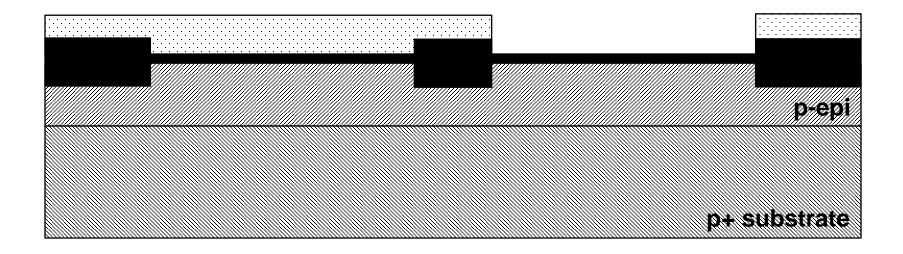
Photolithography





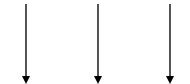
After photolithography

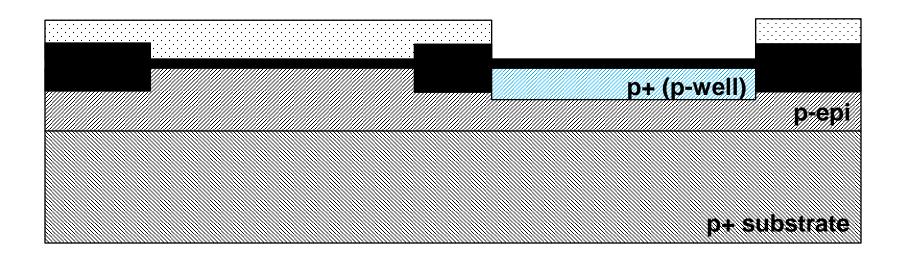




Etching



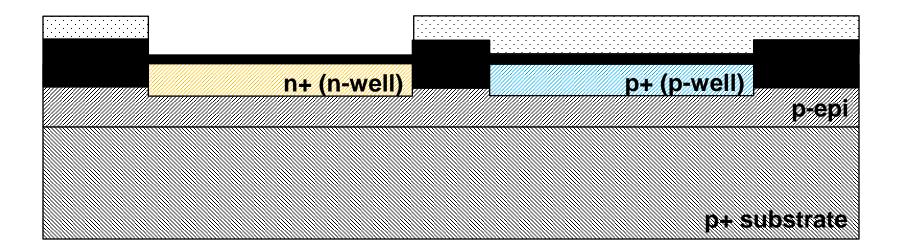




Doping

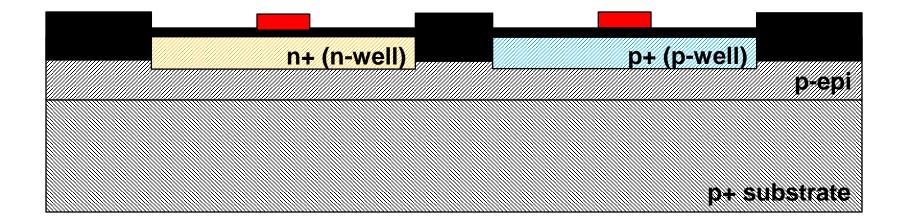






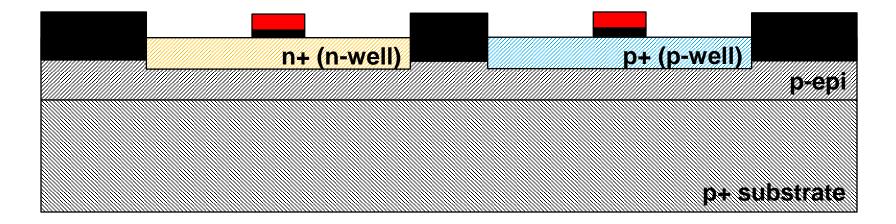
Doping





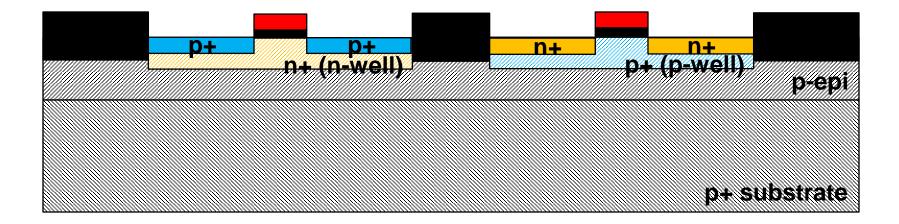
Poly





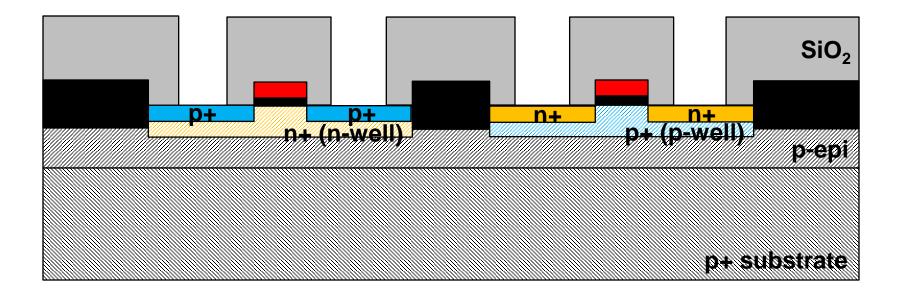
Etching





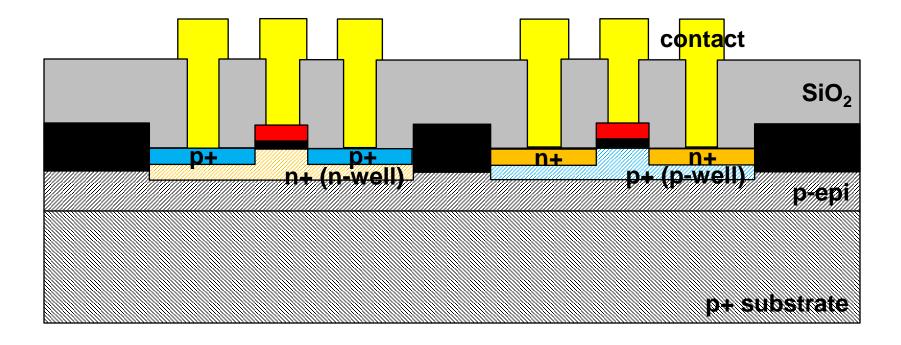
Doping





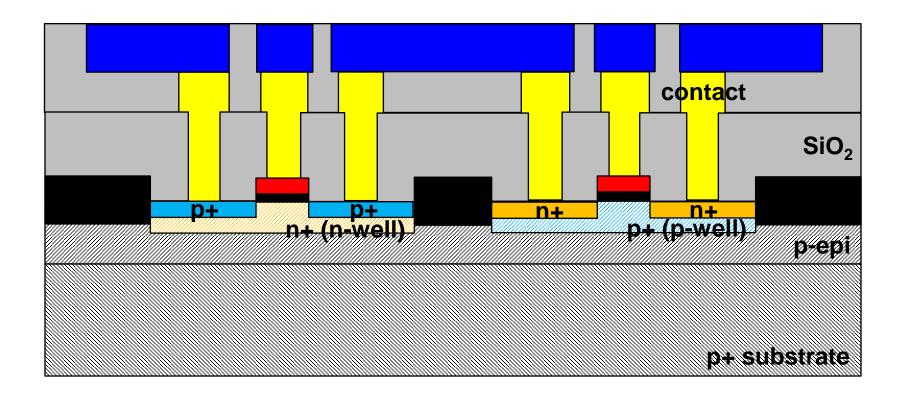
Oxide deposition





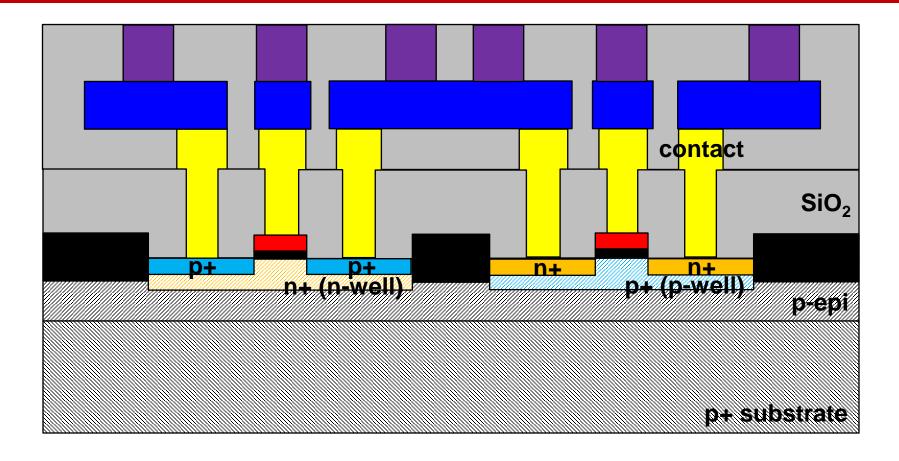
Contact





Metal 1





Via12

